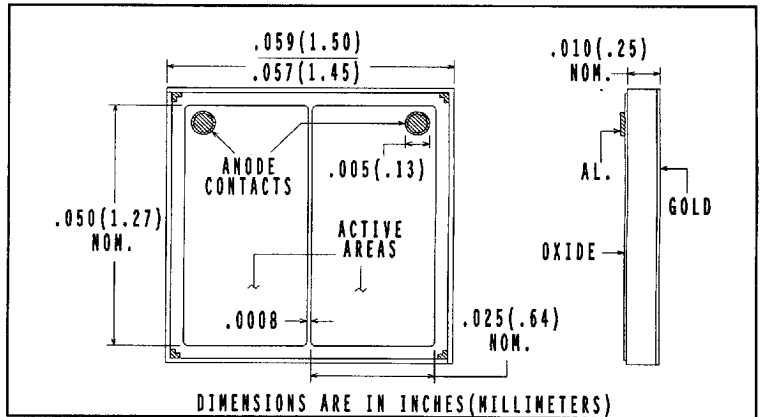
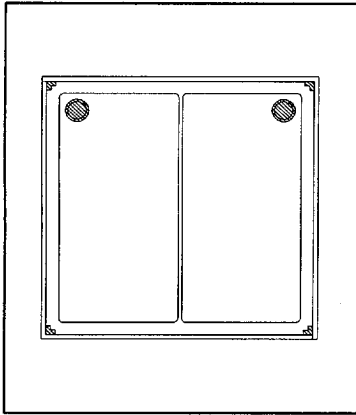


Dual Element Silicon PN Photodiode Type OPC922



Features

- 25 mil x 50 mil PN photodiode elements
- Silicon nitride passivation
- Anti-reflective coating

Description

Dual photodiodes are useful in a variety of motion sensing and control applications ranging from encoding to position sensing. Optek's photodiodes may be operated from zero bias (photovoltaic) up to the diode's reverse breakdown voltage.

Optek chip warranty excludes any damage resulting from improper bonding or alloying techniques.

Packaging Options

OPC922TP Sawn on Tape
 OPC922WP Waffle Pack
 OPC922SP Unsawn Slice
 Special packaging and testing available upon request.

Absolute Maximum Ratings⁽¹⁾ (T_A = 25° C unless otherwise noted)

Operating Temperature -40° C to +85° C
 Storage Temperature -65° C to +120° C
 Reverse Breakdown Voltage 40 V
 Power Dissipation 150 mW⁽²⁾

Electrical Characteristics Per Element (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
V _{(BR)R}	Reverse Breakdown Voltage	40	70		V	I _R = 100 μA
I _D	Reverse Dark Current		<1	10	nA	V _R = 15 V
R _λ	Responsivity	0.35	0.5		A/W	Φ = 10 μW, V _R = 0 V ⁽³⁾
C _T	Capacitance		50		pF	V _R = 1 V, Φ = 0

Notes: (1) All maximum ratings are determined with the chip mounted on a TO-15 header using Optek techniques. (2) Maximum power dissipation is a function of the package in which the chip is housed and the environment in which the assembled package will be used. (3) Light source is a GaAs LED, λ_P = 935 nm, typical.

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